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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	10/691,055
Filing Date	October 22, 2003
First Named Inventor	Kryliouk et al.
Art Unit	
Examiner Name	
Attorney Docket Number	5853-414

Sheet	1	of	2
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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SWC		NIKISHIN et al., "High quality GaN grown on Si(111) by gas source molecular beam epitaxy with ammonia," Applied Physics Letters, 75:2073-2075, 1999	
		ZHANG et al., "Enhanced optical emission from GaN films grown on a silicon substrate," Applied Physics Letters, 74:1984-1986, 1999	
		LINTHICUM et al., "PROCESS ROUTES FOR LOW DEFECT-DENSITY GAN ON VARIOUS SUBSTRATES EMPLOYING PENDEO-EPITAXIAL GROWTH TECHNIQUES," MRS Internet J. Nitride Semicond. Res. 4S1, G4.9, 1999	
		STRITTMATTER et al., "Low-pressure metal organic chemical vapor deposition of GaN on silicon(111) substrates using an AlAs nucleation layer," Applied Physics Letters, 74:1242-1244, 1999	
		SANCHEZ-GARCIA et al., "Ultraviolet electroluminescence in GaN/AlGaIn single-heterojunction light-emitting diodes grown on Si(111)," Journal of Applied Physics, 87:1569-1571, 2000	
		NISHIMURA et al., "Growth of GaN on Si substrates-roles of BP thin layer," Optical Materials, 19:223-228, 2002.	
		NISHIMURA et al., "Low temperature growth interface for growing Boron Monophosphide on Si substrates," Applied Surface Science, 159-160:288-291, 2000.	
		NISHIMURA et al., "Growth of c-GaN on Si(100)," Materials Science and Engineering," B82:25-26, 2001.	
		IZUMIYA et al., "Growth of BP and GaN/BP heterostructures," Proceedings of the 19th International Symposium on Gallium Arsenide and Related Compounds, 157-162, 1993.	
SWC		NISHINAGA et al., "Effect of Growth Parameters on the Epitaxial Growth of BP on Si Substrate," Japanese Journal of Applied Physics, 14:753-760, 1975.	

Examiner Signature	CRANE	Date Considered	9/04
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SWC		LANDOLT-BORNSTEIN, "Semiconductors," 3:14-28 and 43-50.	
		WELKER et al., "Solid State Physics," Group III-Group V Compounds, 1-78, 1956.	
		Johnson, S., "CHAPTER 3 GROWTH OF BP BY CVD" Ph.D. Thesis, 2001.	
SWC		TERASHIMA et al., "Proceedings of the 8th International Symposium on Silicon Materials Science and Technology," 2:44-45, 1998.	

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